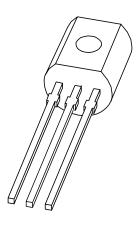
DISCRETE SEMICONDUCTORS

DATA SHEET



BF420; **BF422** NPN high-voltage transistors

Product data sheet Supersedes data of 1996 Dec 09 2004 Nov 10



NPN high-voltage transistors

BF420; BF422

FEATURES

• Low feedback capacitance.

APPLICATIONS

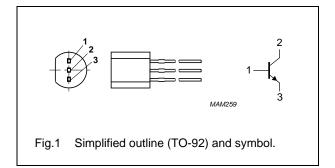
• Class-B video output stages in colour television and professional monitor equipment.

DESCRIPTION

NPN transistors in a TO-92 plastic package. PNP complements: BF421 and BF423.

PINNING

PIN	DESCRIPTION			
1	base			
2	collector			
3	emitter			



ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
TIPE NOWIBER	NAME	DESCRIPTION	VERSION
BF420	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BF422			

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BF420		_	300	V
	BF422		_	250	V
V_{CEO}	collector-emitter voltage	open base			
	BF420		_	300	V
	BF422		_	250	V
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	-	830	mW
h _{FE}	DC current gain	V _{CE} = 20 V; I _C = 25 mA	50	-	
C _{re}	feedback capacitance	$V_{CE} = 30 \text{ V}; I_{C} = I_{c} = 0 \text{ A}; f = 1 \text{ MHz}$	-	1.6	pF
f _T	transition frequency	V _{CE} = 10 V; I _C = 10 mA; f = 100 MHz	60	_	MHz

NPN high-voltage transistors

BF420; BF422

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF420		_	300	V
	BF422		_	250	V
V _{CEO}	collector-emitter voltage	open base			
	BF420		_	300	V
	BF422		_	250	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	50	mA
I _{CM}	peak collector current		_	100	mA
I _{BM}	peak base current		_	50	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	830	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

1. Transistor mounted on a printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Transistor mounted on a printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 200 V; I _E = 0 A	_	10	nA
		$V_{CB} = 200 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	10	μА
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	50	nA
h _{FE}	DC current gain	V _{CE} = 20 V; I _C = 25 mA	50	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 30 \text{ mA}; I_B = 5 \text{ mA}$	-	0.6	V
C _{re}	feedback capacitance	$V_{CE} = 30 \text{ V}; I_{C} = i_{c} = 0 \text{ A}; f = 1 \text{ MHz}$	_	1.6	pF
f _T	transition frequency	V _{CE} = 10 V; I _C = 10 mA; f = 100 MHz	60	_	MHz

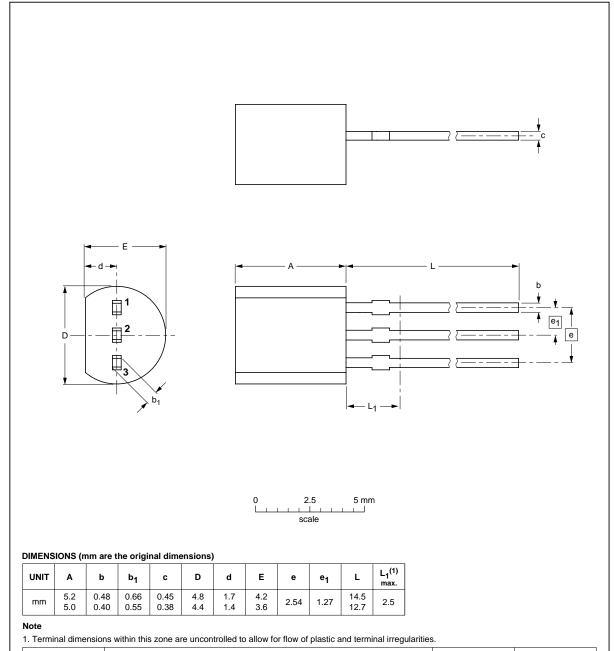
NPN high-voltage transistors

BF420; BF422

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



OUTLINE		REFER	ENCES	EUROPEAN		ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT54		TO-92	SC-43A			-04-06-28 04-11-16

NPN high-voltage transistors

BF420; BF422

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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